Vishay Siliconix



P-Channel 12 V (D-S) MOSFET

PowerPAK® SC-70-6L Single Top View **Bottom View**

Marking code: BR

PRODUCT SUMMARY									
V _{DS} (V)	-12								
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -4.5 \text{ V}$	0.0135								
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -2.5 \text{ V}$	0.0194								
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -1.8 \text{ V}$	0.0344								
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -1.5 \text{ V}$	0.0710								
Q _g typ. (nC)	31								
I _D (A) ^a	-12								
Configuration	Single								

FEATURES

- TrenchFET® power MOSFET
- Thermally enhanced PowerPAK® SC-70 package
 - Small footprint area
 - Low on-resistance
- 100 % R_a tested

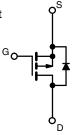
• Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

RoHS

HALOGEN FREE

APPLICATIONS

- Providing low voltage drop in smart phones, tablet PCs, mobile computing:
 - Battery switches
 - Battery management
 - Load switches



P-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK SC-70
Load (Dh) free and balagen free	SiA447DJ-T4-GE3
Lead (Pb)-free and halogen-free	SiA447DJ-T1-GE3

PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-source voltage		V _{DS}	-12	V		
Gate-source voltage		V _{GS}	± 8	7 v		
	T _C = 25 °C		-12 ^a			
Continuous drain surrent (T. 150 °C)	T _C = 70 °C	_	-12 ^a			
Continuous drain current (T _J = 150 °C)	T _A = 25 °C	I _D	-12 ^{a, b, c}			
	T _A = 70 °C		-10 ^{b, c}	A		
Pulsed drain current (t = 300 μs)		I _{DM}	-50			
Ocalia a cara della finda a caral	T _C = 25 °C	,	-12 ^a			
Continuous source-drain diode current	T _A = 25 °C	I _S	-2.9 ^{b, c}	\neg		
	T _C = 25 °C		19			
Market and a second production of the	T _C = 70 °C	_	12			
Maximum power dissipation	T _A = 25 °C	P _D	3.5 b, c	- W		
	T _A = 70 °C		2.2 b, c			
Operating junction and storage temperature ra	nge	T _J , T _{stq}	-55 to +150	%0		
Soldering recommendations (peak temperature	e) d, e		260	°C		

THERMAL RESISTANCE RATINGS									
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT				
Maximum junction-to-ambient b, f	t ≤ 5 s	R _{thJA}	28	36	°C/W				
Maximum junction-to-case (drain)	Steady state	R_{thJC}	5.3	6.5	G/VV				

Notes

- a. Package limited
- b. Surface mounted on 1" x 1" FR4 board
- t = 5 s
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- Maximum under steady state conditions is 80 °C/W



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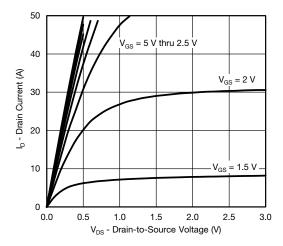
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT			
Static			•						
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0$, $I_D = -250 \mu A$	-12	-	-	V			
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$		-	-7	-	mV/°C			
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	$I_D = -250 \mu A$	-	3	-				
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-0.4	-	-0.85	V			
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$	-	-	± 100	nA			
7		V _{DS} = -12 V, V _{GS} = 0 V	-	-	-1	μΑ			
Zero gate voltage drain current	I _{DSS}	$V_{DS} = -12 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$	-	-	-10				
On-state drain current a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-10	-	-	Α			
	` ′	$V_{GS} = -4.5 \text{ V}, I_D = -7 \text{ A}$	-	0.0110	0.0135				
During a second of the second of the second		$V_{GS} = -2.5 \text{ V}, I_D = -5 \text{ A}$	-	0.0150	0.0194				
Drain-source on-state resistance a	R _{DS(on)}	V _{GS} = -1.8 V, I _D = -3 A	-	0.0230	0.0344	Ω			
		V _{GS} = -1.5 V, I _D = -1 A	-	0.0400	0.0710	7			
Forward transconductance a	9 _{fs}	$V_{DS} = -6 \text{ V}, I_{D} = -7 \text{ A}$	-	35	-	S			
Dynamic ^b	•		•						
Input capacitance	C _{iss}		-	2880	-	pF			
Output capacitance	C _{oss}	$V_{DS} = -6 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	590	-				
Reverse transfer capacitance	C _{rss}		-	585	-				
Table and a share a		$V_{DS} = -6 \text{ V}, V_{GS} = -8 \text{ V}, I_D = -13 \text{ A}$	-	52	80	nC			
Total gate charge	Q_g		-	31	47				
Gate-source charge	Q_{gs}	$V_{DS} = -6 \text{ V}, V_{GS} = -4.5 \text{ V}, I_D = -13 \text{ A}$	-	4.2	-				
Gate-drain charge	Q _{qd}		-	7.8	-				
Gate resistance	Rq	f = 1 MHz	0.8	4.3	8.6	Ω			
Turn-on delay time	t _{d(on)}			30	60				
Rise time	t _r	$V_{DD} = -6 \text{ V}, R_1 = 0.6 \Omega$	-	30	60	ns			
Turn-off delay time	t _{d(off)}	$I_D \cong -10 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$	-	60	120				
Fall time	t _f		-	25	50				
Turn-on delay time	t _{d(on)}		-	12	25				
Rise time	t _r	$V_{DD} = -6 \text{ V}, R_1 = 0.6 \Omega$	-	10	20				
Turn-off delay time	t _{d(off)}	$I_D \cong -10 \text{ A}, V_{GEN} = -8 \text{ V}, R_g = 1 \Omega$	-	65	130				
Fall time	t _f		-	20	40				
Drain-Source Body Diode Characterist	ics		•						
Continuous source-drain diode current	Is	T _C = 25 °C	-	-	-12				
Pulse diode forward current	I _{SM}		-	-	-50	Α			
Body diode voltage	V _{SD}	I _S = -10 A, V _{GS} = 0 V	-	-0.8	-1.2	V			
Body diode voltage Body diode reverse recovery time t _{rr}		<u> </u>	-	25	50	ns			
Body diode reverse recovery charge	Q _{rr}	$I_F = -10 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s},$	_	7.5	15	nC			
Reverse recovery fall time	t _a	$T_{\rm J} = 25 ^{\circ}{\rm C}$	_	8	-	†			
			1						

Notes

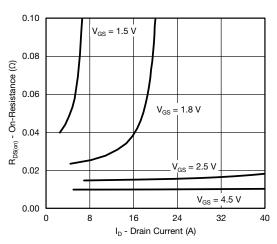
- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2%
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability

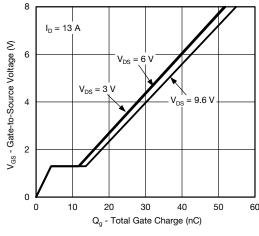




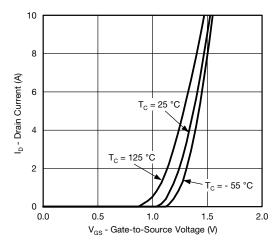
Output Characteristics



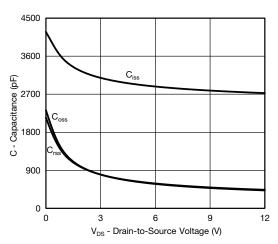
On-Resistance vs. Drain Current and Gate Voltage



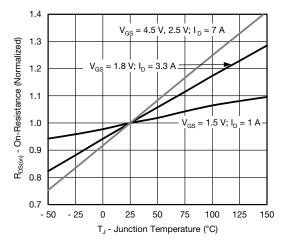
Gate Charge



Transfer Characteristics

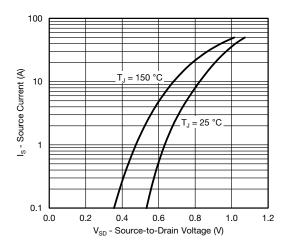


Capacitance

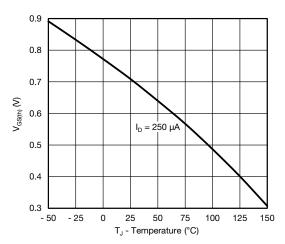


On-Resistance vs. Junction Temperature

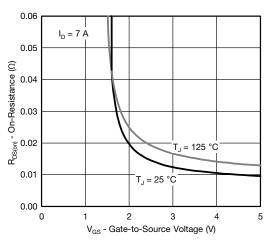




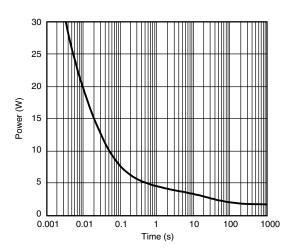
Source-Drain Diode Forward Voltage



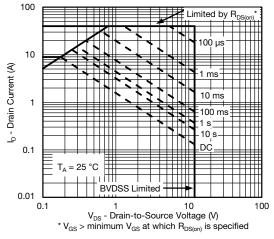
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage

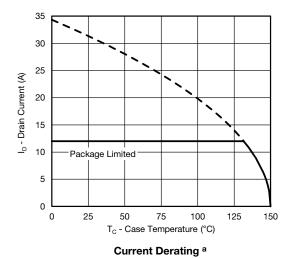


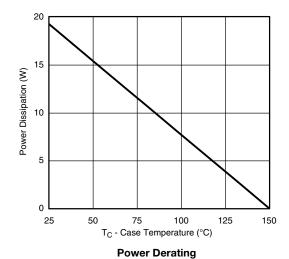
Single Pulse Power, Junction-to-Ambient



Safe Operating Area, Junction-to-Ambient



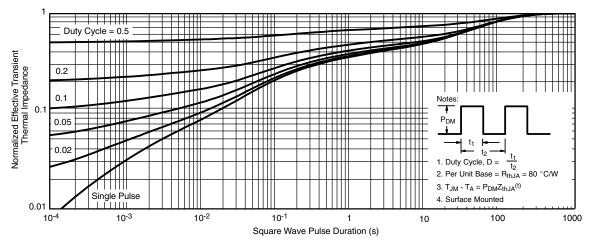




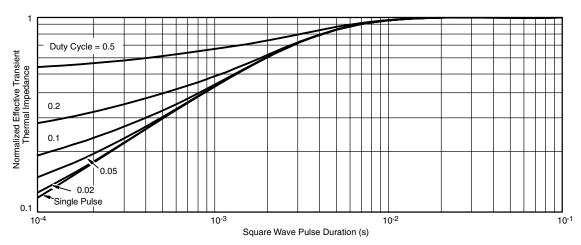
Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit





Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

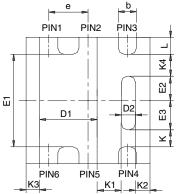
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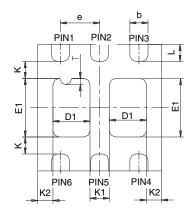




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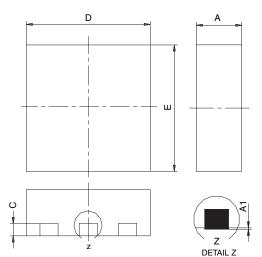
PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

	SINGLE PAD							DUAL PAD				
DIM	M	ILLIMETER	RS		INCHES		М	ILLIMETER	RS		INCHES	
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A 1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D2	0.135	0.235	0.335	0.005	0.009	0.013						
Е	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E2	0.345	0.395	0.445	0.014	0.016	0.018						
E3	0.425	0.475	0.525	0.017	0.019	0.021						
е		0.65 BSC			0.026 BSC	;		0.65 BSC			0.026 BSC	
K		0.275 TYP			0.011 TYP	1	0.275 TYP			0.011 TYP		
K1		0.400 TYP			0.016 TYP		0.320 TYP			0.013 TYP		
K2		0.240 TYP		0.009 TYP		0.252 TYP			0.010 TYP			
К3		0.225 TYP		0.009 TYP								
K4		0.355 TYP		0.014 TYP								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
Т							0.05	0.10	0.15	0.002	0.004	0.006
ECN: C O	2.07/21 Pay C 06 Aug 07											

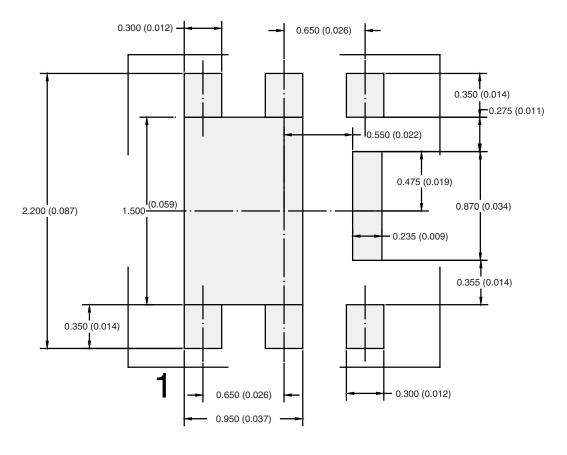
ECN: C-07431 - Rev. C, 06-Aug-07

DWG: 5934

Document Number: 73001 06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

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